

NPN-Silizium-Fototransistor
Silicon NPN Phototransistor
Lead (Pb) Free Product - RoHS Compliant

BPY 62



Wesentliche Merkmale

- Speziell geeignet für Anwendungen im Bereich von 400 nm bis 1100 nm
- Hohe Linearität
- Hermetisch dichte Metallbauform (TO-18) mit Basisanschluss, geeignet bis 125 °C
- Gruppierbar

Anwendungen

- Lichtschranken für Gleich- und Wechsellichtbetrieb
- Industrieelektronik
- „Messen/Steuern/Regeln“

Features

- Especially suitable for applications from 400 nm to 1100 nm
- High linearity
- Hermetically sealed metal package (TO-18) with base connection, suitable up to 125 °C
- Available in groups

Applications

- Photointerrupters
- Industrial electronics
- For control and drive circuits

Typ Type	Bestellnummer Ordering Code	Fotostrom , $E_e = 0.5 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$, $V_{CE} = 5 \text{ V}$ Photocurrent $I_{PCE} \text{ (mA)}$
BPY 62	Q60215Y0062	> 0.5
BPY 62-3	Q60215Y1112	0.8...1.6
BPY 62-3/4	Q60215Y5198	0.8...2.5
BPY 62-4	Q60215Y1113	1.25...2.5

Grenzwerte
Maximum Ratings

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 125	°C
Kollektor-Emitterspannung Collector-emitter voltage	V_{CE}	35	V
Kollektorstrom Collector current	I_C	100	mA
Kollektorspitzenstrom, $\tau < 10 \mu s$ Collector surge current	I_{CS}	200	mA
Emitter-Basisspannung Emitter-base voltage	V_{EB}	7	V
Verlustleistung, $T_A = 25 \text{ °C}$ Total power dissipation	P_{tot}	200	mW
Wärmewiderstand Thermal resistance	R_{thJA}	500	K/W

Kennwerte ($T_A = 25\text{ °C}$, $\lambda = 950\text{ nm}$)

Characteristics

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{S\text{ max}}$	830	nm
Spektraler Bereich der Fotoempfindlichkeit $S = 10\%$ von S_{max} Spectral range of sensitivity $S = 10\%$ of S_{max}	λ	400 ... 1100	nm
Bestrahlungsempfindliche Fläche Radiant sensitive area	A	0.11	mm ²
Abmessung der Chipfläche Dimensions of chip area	$L \times B$ $L \times W$	0.5×0.5	mm \times mm
Halbwinkel Half angle	φ	± 8	Grad deg.
Fotostrom der Kollektor-Basis-Fotodiode Photocurrent of collector-base photodiode $E_e = 0.5\text{ mW/cm}^2$, $V_{CB} = 5\text{ V}$ $E_v = 1000\text{ lx}$, Normlicht/standard light A, $V_{CB} = 5\text{ V}$	I_{PCB} I_{PCB}	5.5 17	μA μA
Kapazität Capacitance $V_{CE} = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$ $V_{CB} = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$ $V_{EB} = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$	C_{CE} C_{CB} C_{EB}	7.5 14 19	pF pF pF
Dunkelstrom Dark current $V_{CE} = 20\text{ V}$, $E = 0$	I_{CEO}	1 (≤ 50)	nA

Die Fototransistoren werden nach ihrer Fotoempfindlichkeit gruppiert und mit arabischen Ziffern gekennzeichnet.

The phototransistors are grouped according to their spectral sensitivity and distinguished by arabian figures.

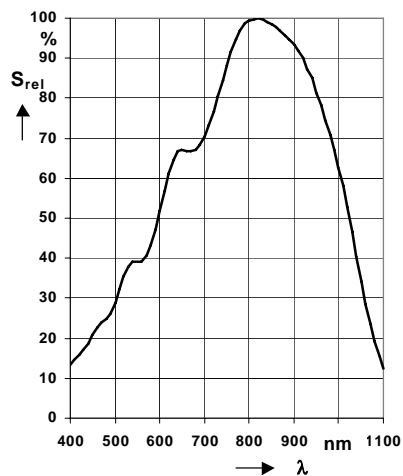
Bezeichnung Parameter	Symbol Symbol	Wert Value				Einheit Unit
		-2	-3	-4	-5	
Fotostrom Photocurrent $E_e = 0.5 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$, $V_{CE} = 5 \text{ V}$ $E_v = 1000 \text{ lx}$, Normlicht/standard light A, $V_{CE} = 5 \text{ V}$	I_{PCE} I_{PCE}	0.5...1.0 2.4	0.8...1.6 3.8	1.25...2.5 5.8	≥ 2.0 9.6	mA mA
Anstiegszeit/Abfallzeit Rise and fall time $I_C = 1 \text{ mA}$, $V_{CC} = 5 \text{ V}$, $R_L = 1 \text{ k}\Omega$	t_r , t_f	5	7	9	12	μs
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage $I_C = I_{PCEmin}^{1)} \times 0.3$, $E_e = 0.5 \text{ mW/cm}^2$	V_{CEsat}	150	150	160	180	mV
Stromverstärkung Current gain $E_e = 0.5 \text{ mW/cm}^2$, $V_{CE} = 5 \text{ V}$	$\frac{I_{PCE}}{I_{PCB}}$	140	220	340	550	–

¹⁾ I_{PCEmin} ist der minimale Fotostrom der jeweiligen Gruppe.

¹⁾ I_{PCEmin} is the min. photocurrent of the specified group.

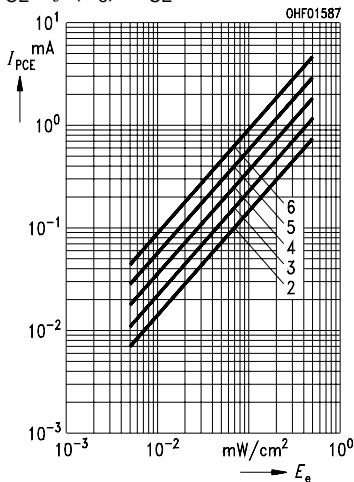
Relative Spectral sensitivity

$S_{rel} = f(\lambda)$



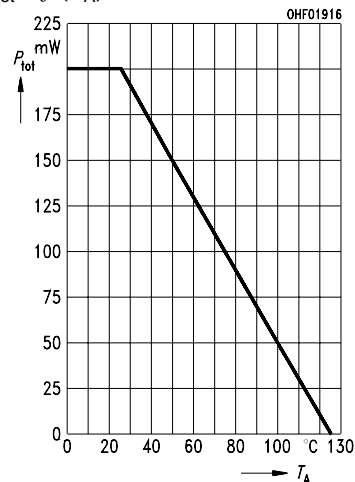
Photocurrent

$I_{PCE} = f(E_e), V_{CE} = 5 V$



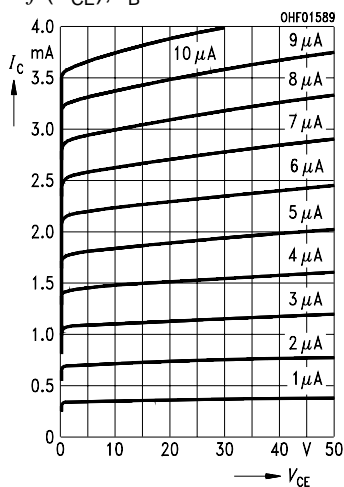
Total Power Dissipation

$P_{tot} = f(T_A)$



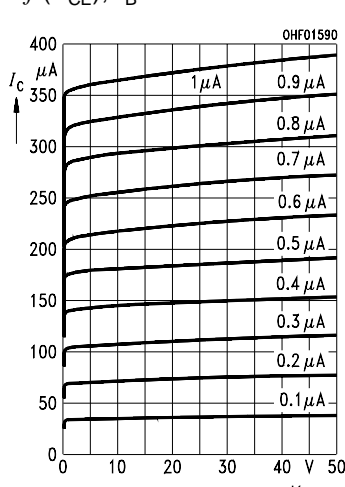
Output Characteristics

$I_C = f(V_{CE}), I_B = \text{Parameter}$



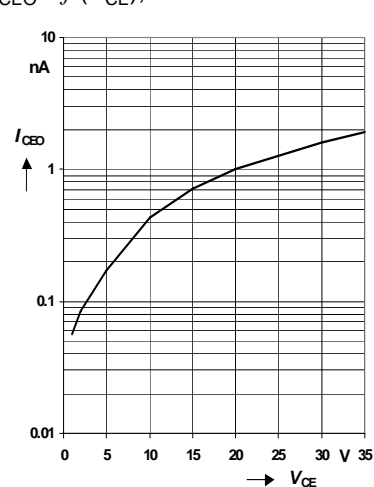
Output Characteristics

$I_C = f(V_{CE}), I_B = \text{Parameter}$



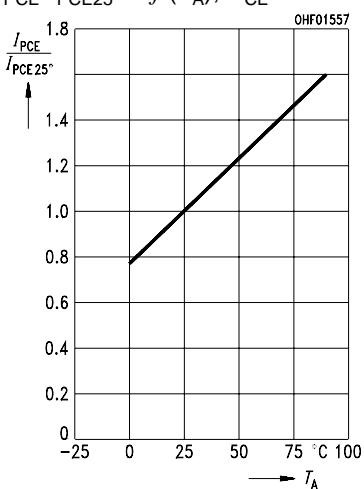
Dark Current

$I_{CEO} = f(V_{CE}), E = 0$



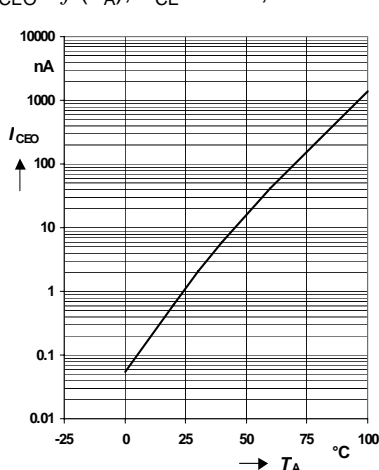
Photocurrent

$I_{PCE}/I_{PCE25^\circ} = f(T_A), V_{CE} = 5 V$



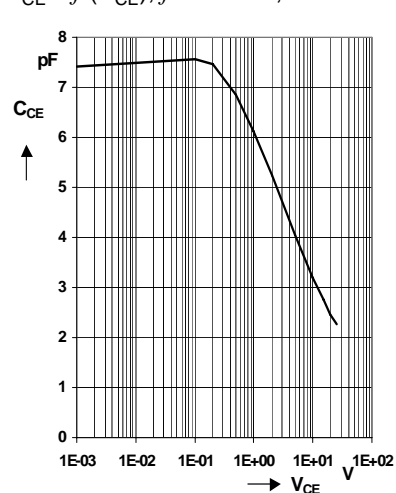
Dark Current

$I_{CEO} = f(T_A), V_{CE} = 20 V, E = 0$



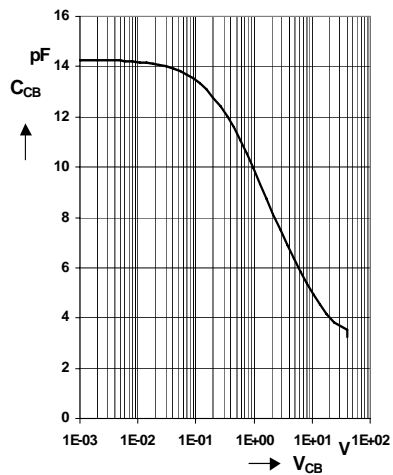
Collector-Emitter Capacitance

$C_{CE} = f(V_{CE}), f = 1 \text{ MHz}, E = 0$



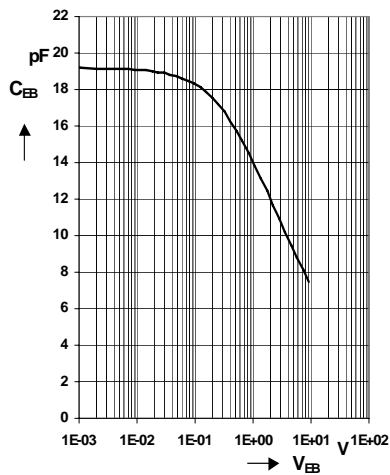
Collector-Base Capacitance

$C_{CB} = f(V_{CB}), f = 1 \text{ MHz}, E = 0$



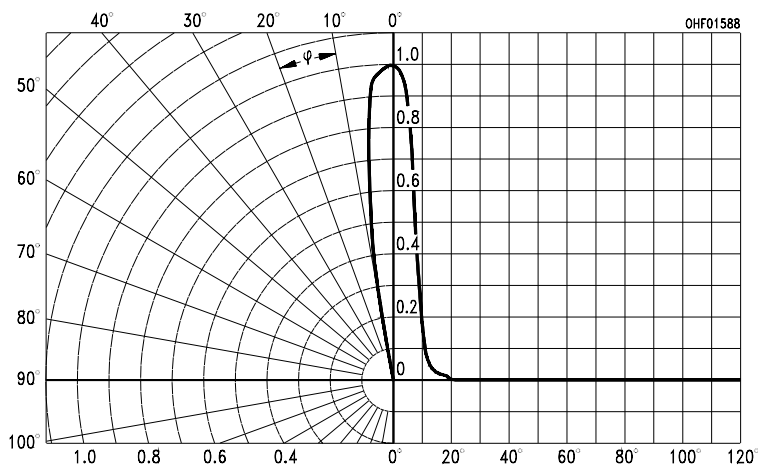
Emitter-Base Capacitance

$C_{EB} = f(V_{EB}), f = 1 \text{ MHz}, E = 0$

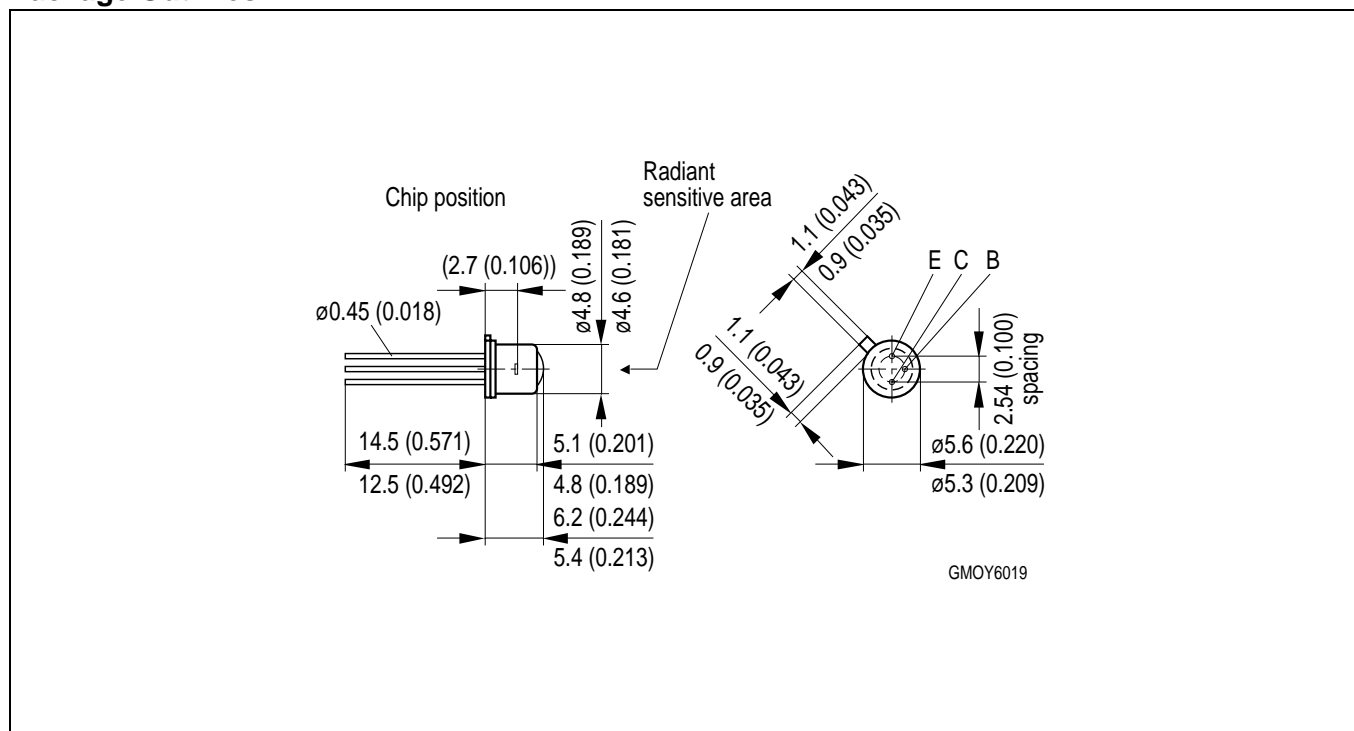


Directional Characteristics

$S_{rel} = f(\varphi)$



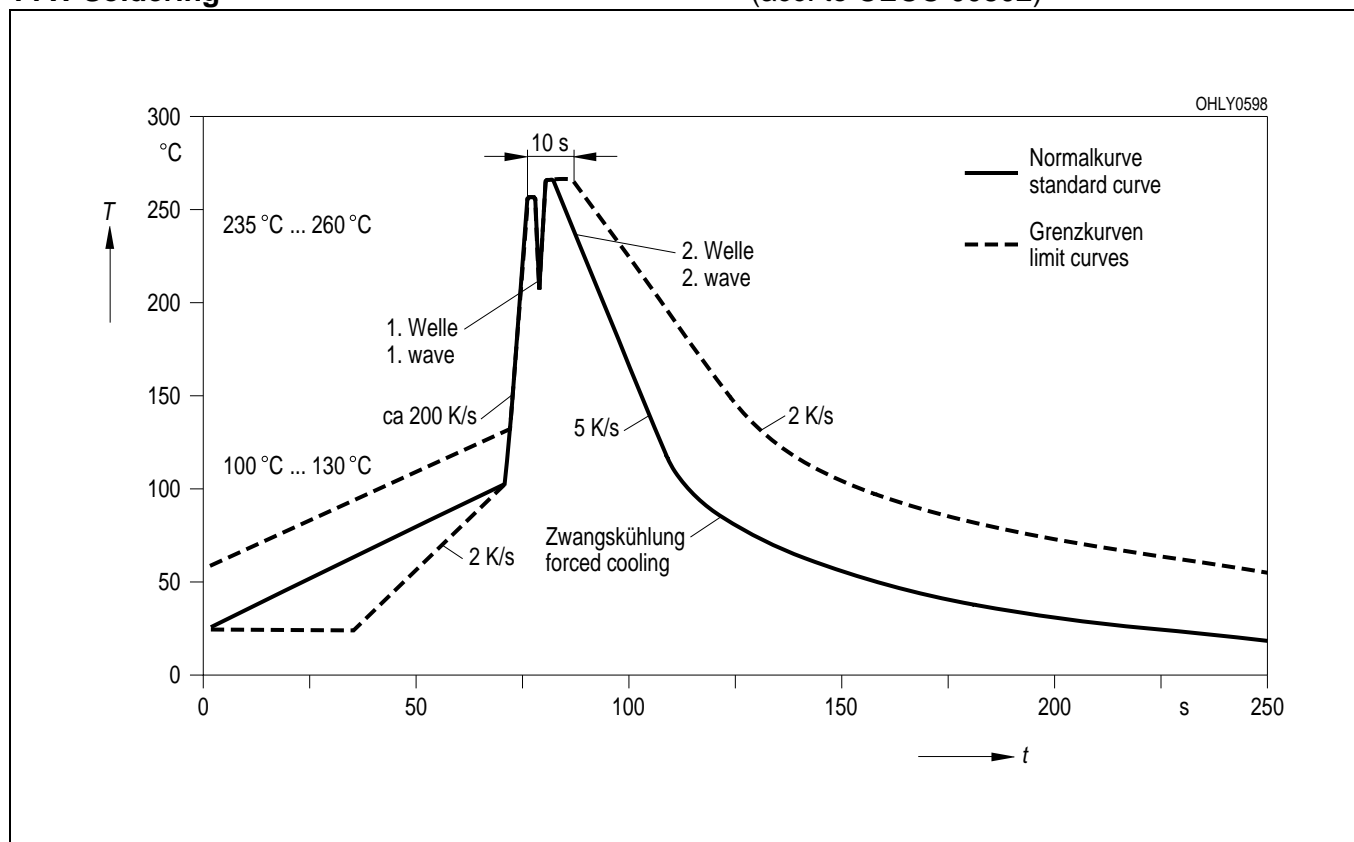
Maßzeichnung
Package Outlines



Maße in mm (inch) / Dimensions in mm (inch).

Lötbedingungen
Soldering Conditions
Wellenlöten (TTW)
TTW Soldering

(nach CECC 00802)
 (acc. to CECC 00802)



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